

ABSTRACT

In a method of manufacturing a crystallized semiconductor device of the present invention, a thermal diffusion layer (1) having higher thermal conductivity than that of a substrate (4) is formed on a surface of a semiconductor layer (2), and then laser light is applied to the semiconductor layer (2) from above the thermal diffusion layer (1). As a result, it becomes possible to manufacture the crystallized semiconductor device in which a crystal is longer than that of a conventional arrangement. According to the present invention, it is possible to provide the crystallized semiconductor device having the semiconductor layer in which the size of the crystal grain is larger than that of the conventional arrangement.